

SANYO

No.930C

2SB892/2SD1207

PNP/NPN Epitaxial Planar Silicon Transistors

Large-Current Switching Applications**APPLICATIONS**

- Power supplies, relay drivers, lamp drivers, and automotive wiring

FEATURES

- FBET and MBIT processed (Original process of SANYO)
- Low saturation voltage
- Large current capacity and wide ASO

Values for 2SB892 shown in ()

ABSOLUTE MAXIMUM RATINGS/ $T_a=25^{\circ}\text{C}$

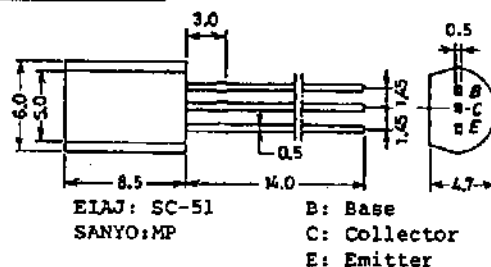
			unit
Collector to base voltage	V_{CBO}	(-)60	V
Collector to emitter voltage	V_{CEO}	(-)50	V
Emitter to base voltage	V_{EBO}	(-)6	V
Collector current	I_C	(-)2	A
Collector Current(Pulse)	I_{CP}	(-)4	A
Allowable collector dissipation	P_C	1	W
Junction temperature	T_j	150	$^{\circ}\text{C}$
Storage ambient temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS/ $T_a=25^{\circ}\text{C}$

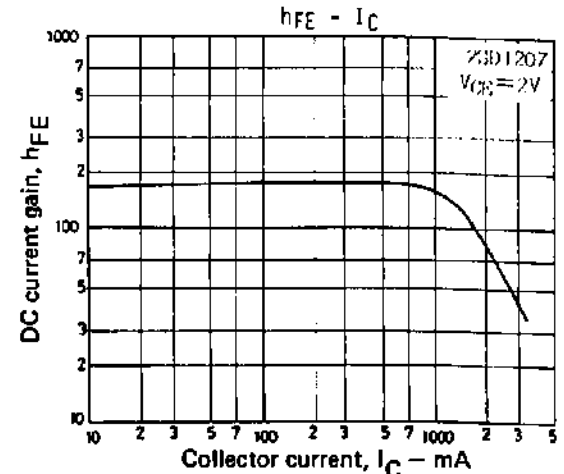
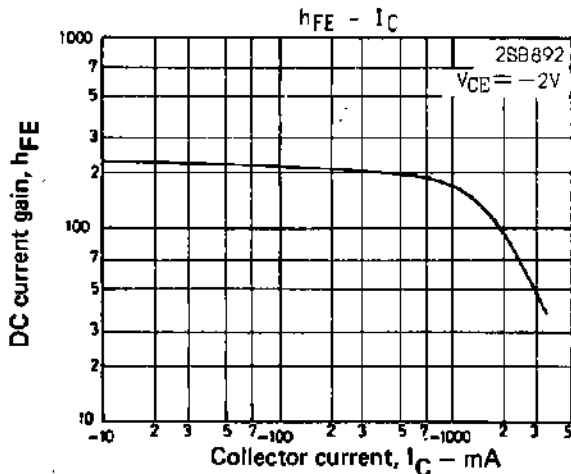
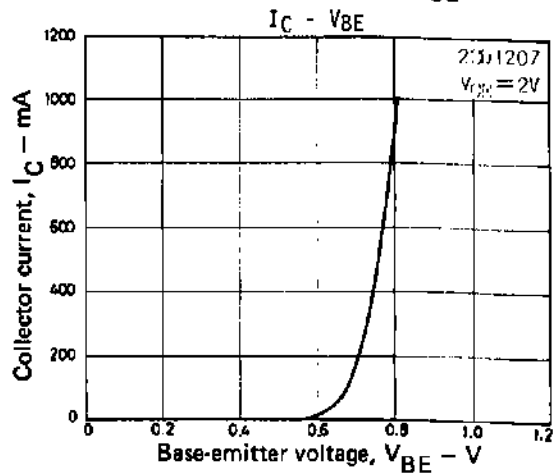
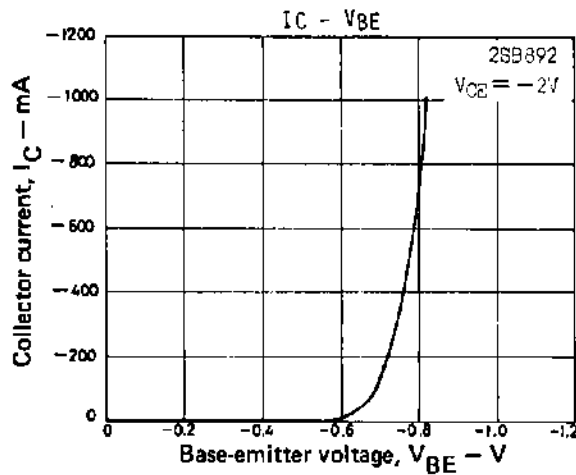
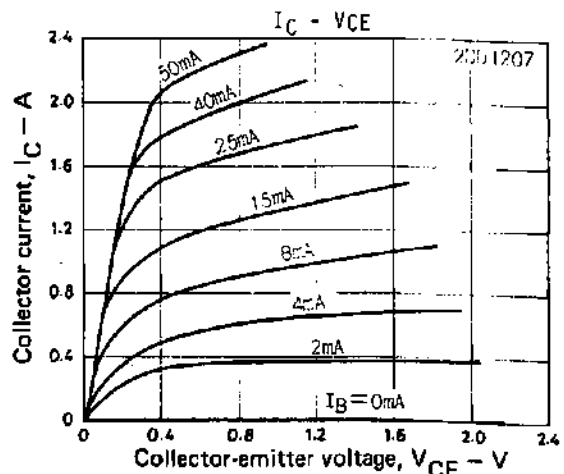
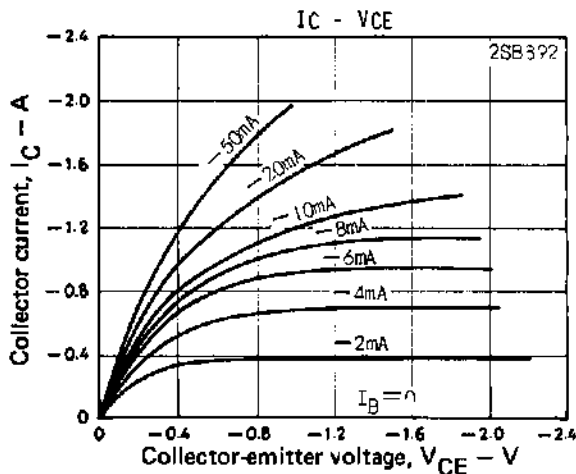
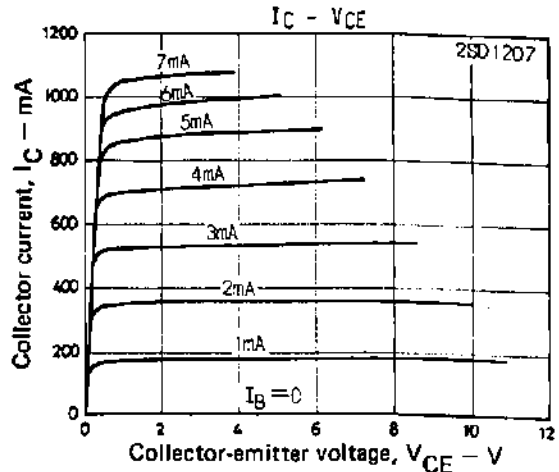
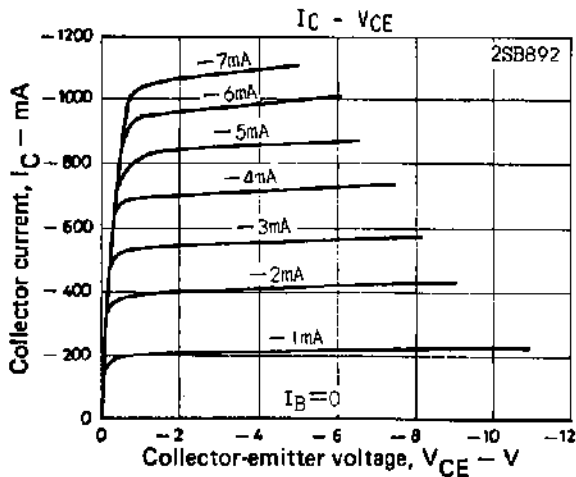
			min	typ	max	unit
Collector cut-off current	I_{CBO}	$V_{CB}=(-)50\text{V}, I_E=0$			(-)0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-)0.1	μA
DC current gain	$h_{FE(1)*}$	$V_{CE}=(-)2\text{V}, I_C=(-)100\text{mA}$	100		560	
	$h_{FE(2)}$	$V_{CE}=(-)2\text{V}, I_C=(-)1.5\text{A}$	40			
Gain-bandwidth product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		150		MHz
Output capacitance	c_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		12		pF
				(22)		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=(-)1\text{A}, I_B=(-)50\text{mA}$		0.15	0.4	V
				(-0.3)	(-0.7)	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=(-)1\text{A}, I_B=(-)50\text{mA}$			(-)0.9 (-)1.2	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)6			V

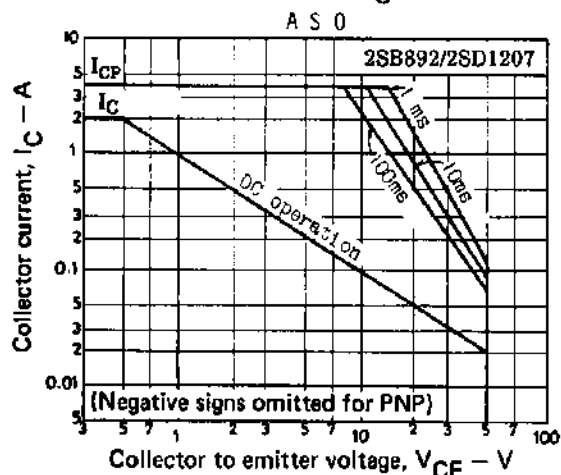
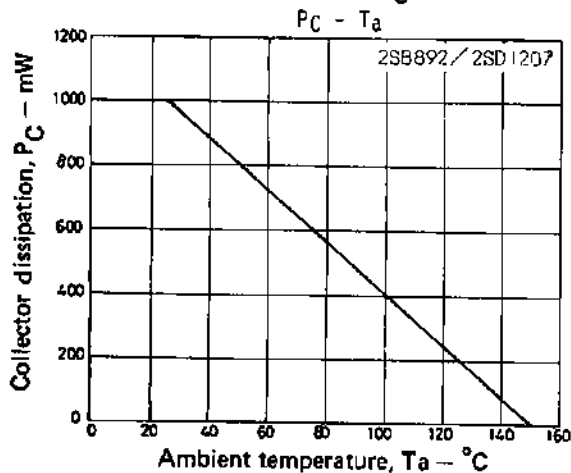
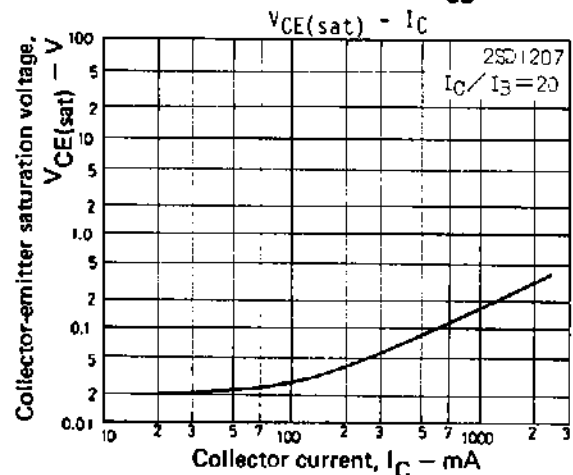
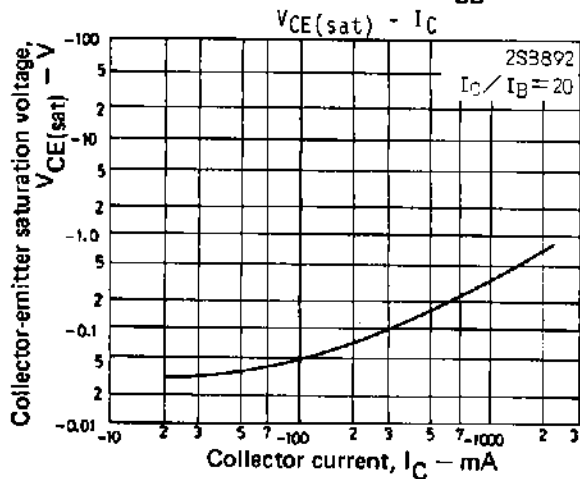
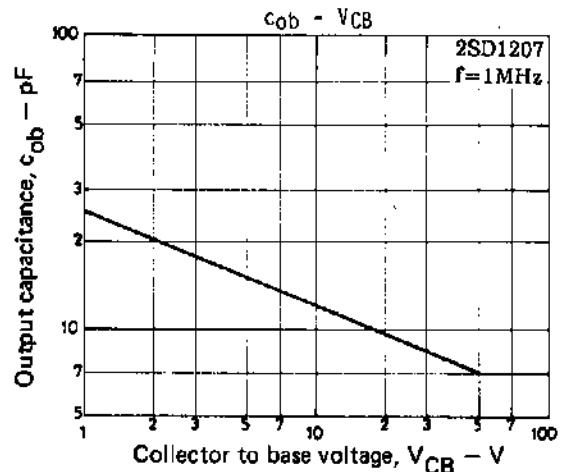
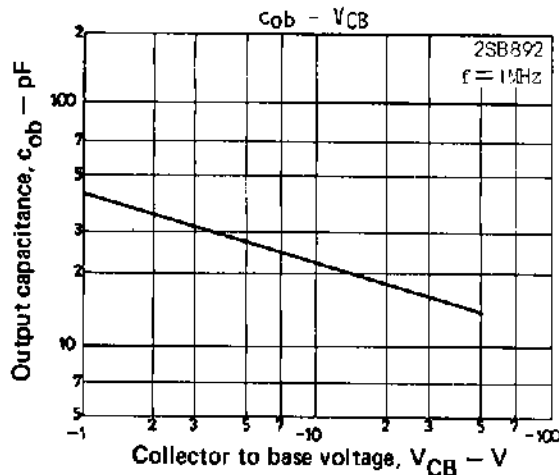
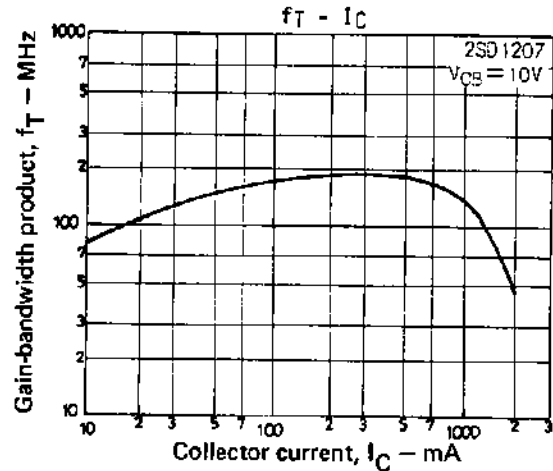
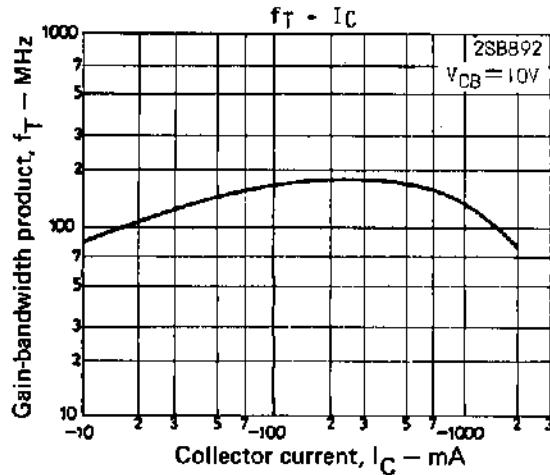
* 2SB892 and 2SD1207 are graded as follows by h_{FE} at 100mA:

100	R	200	140	S	280	200	T	400	280	U	560
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Package Dimensions 2006A
(unit: mm)**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

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